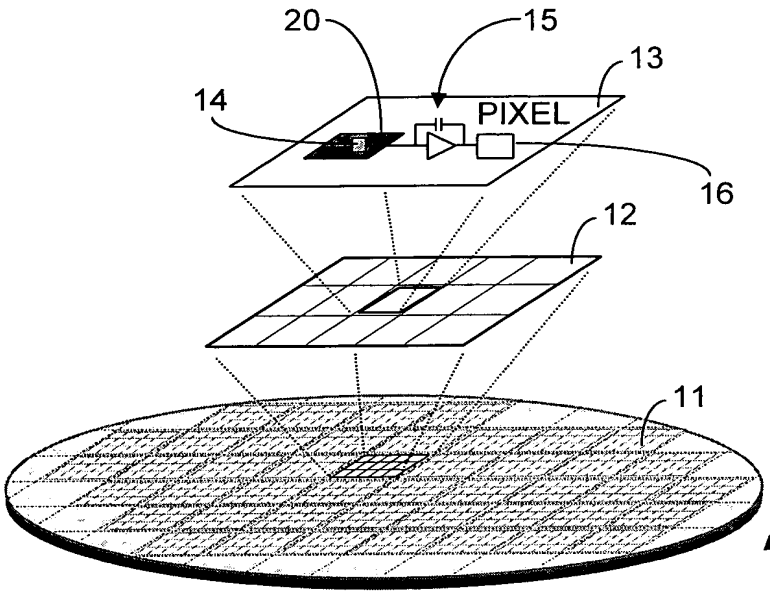

FIG. 1
(PRIOR ART)

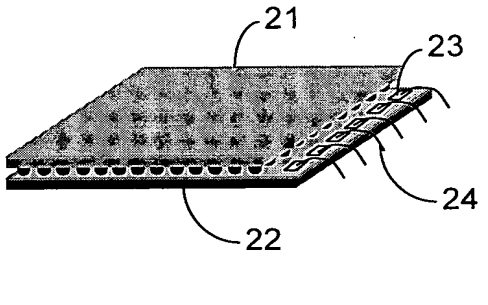

FIG. 2
(PRIOR ART)

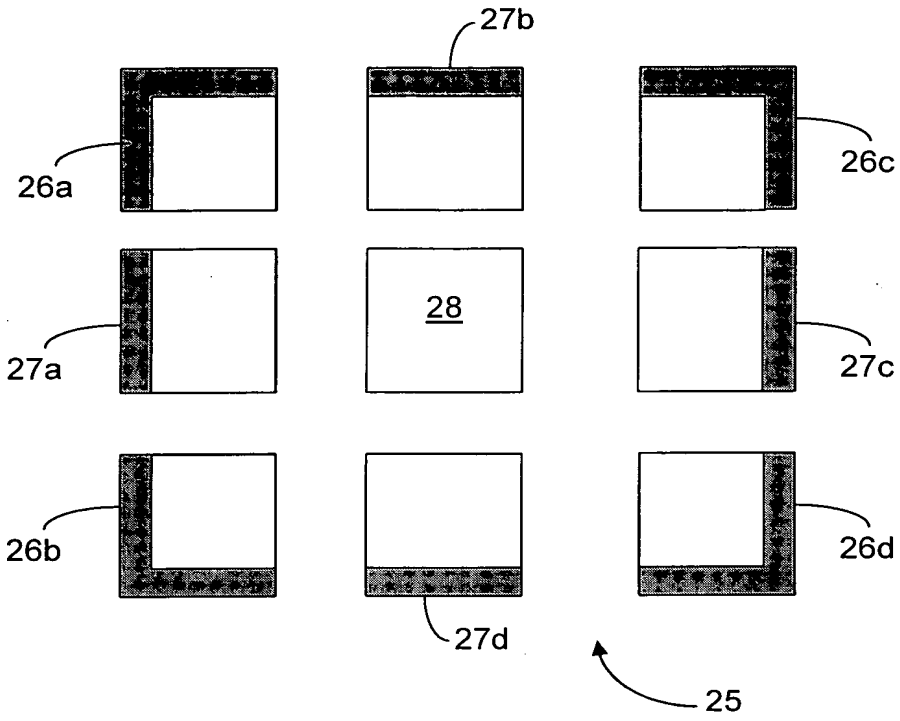
27b
26a
26c
28
27a
27c
26b
26d
27d
25

FIG. 3

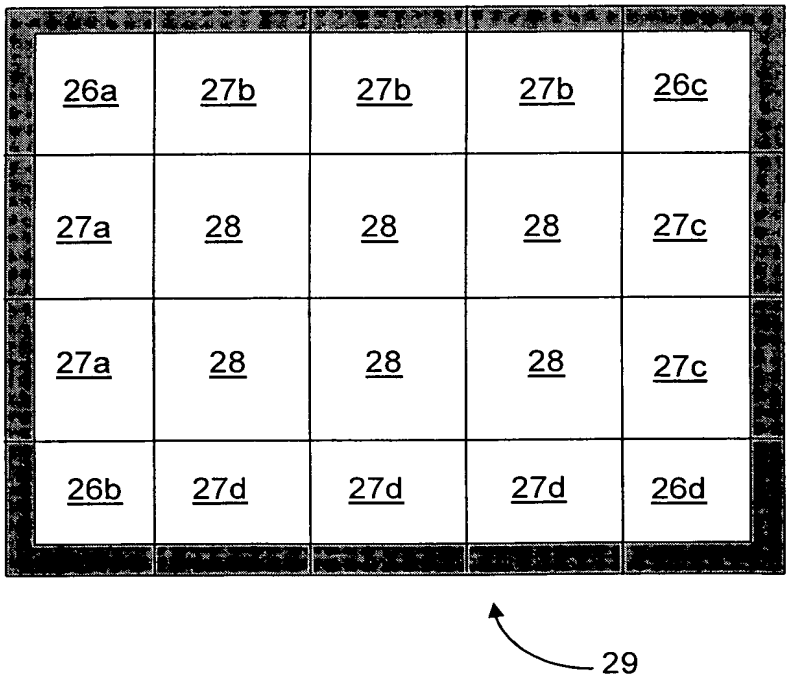
26a
27b
27b
27b
26c
27a
28
28
28
27c
27a
28
28
28
27c
26b
27d
27d
27d
26d
29

FIG. 4

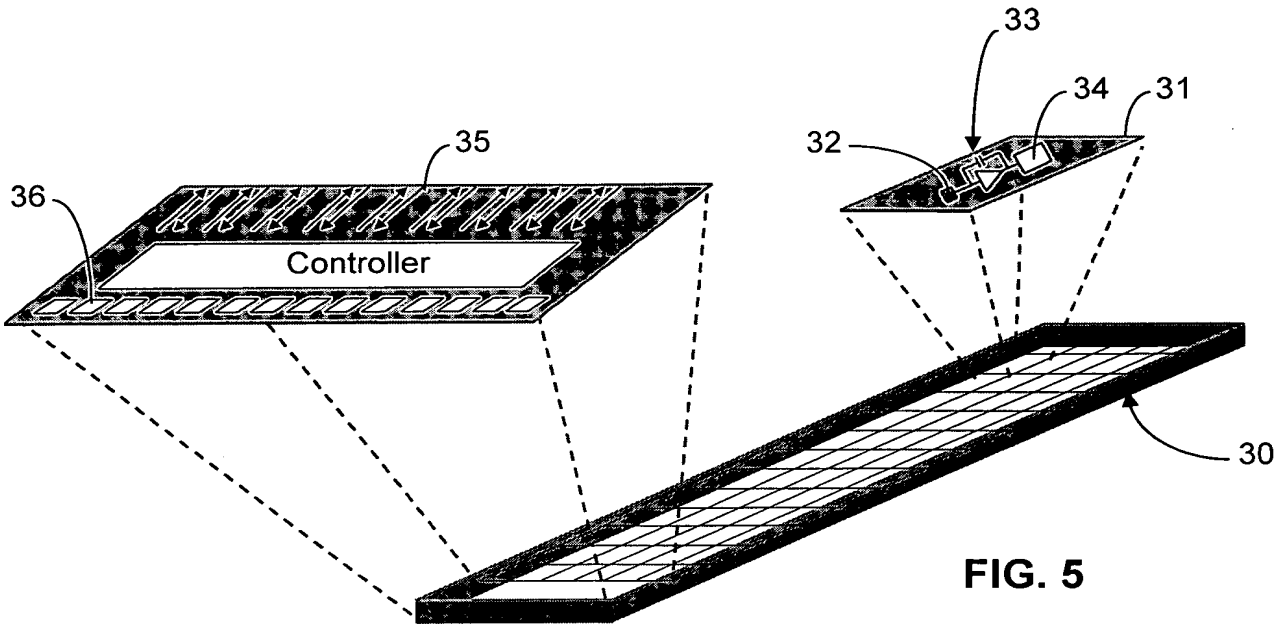

FIG. 5

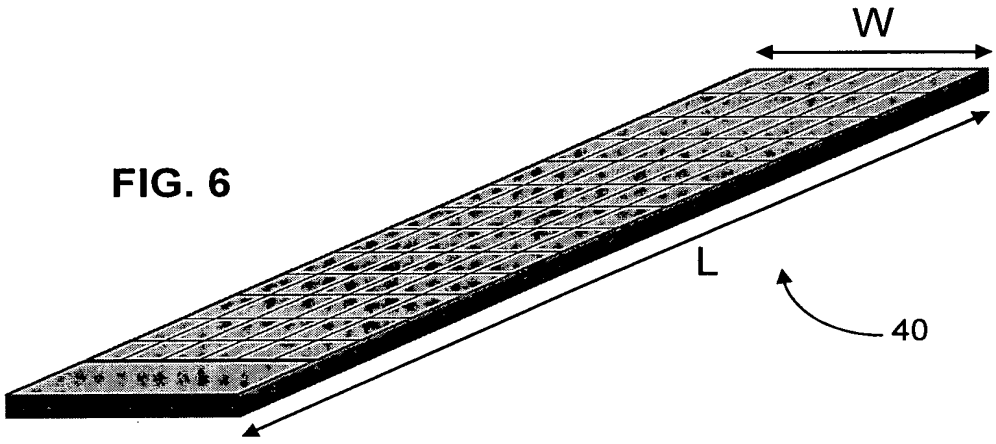

FIG. 6

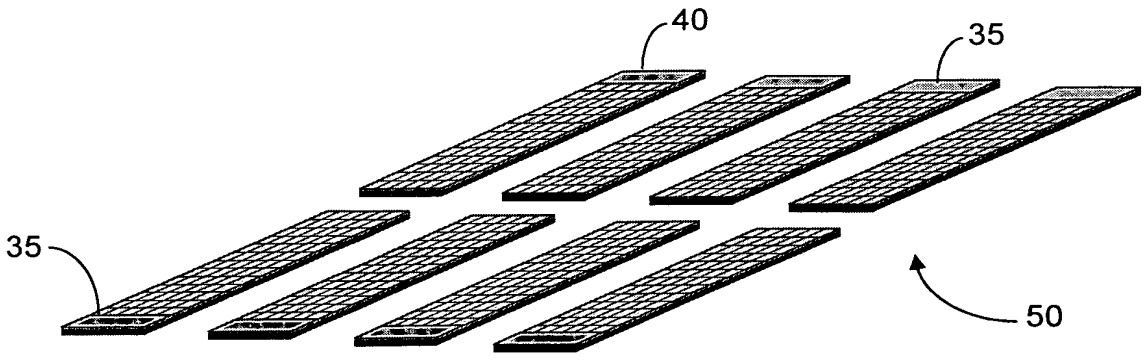

FIG. 7

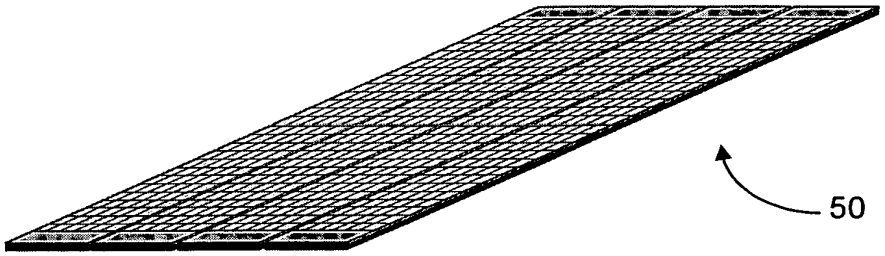

FIG. 8

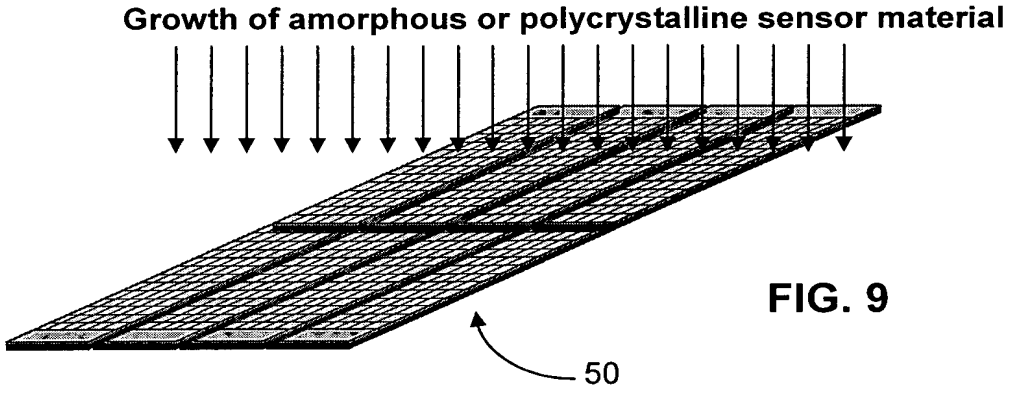

FIG. 9

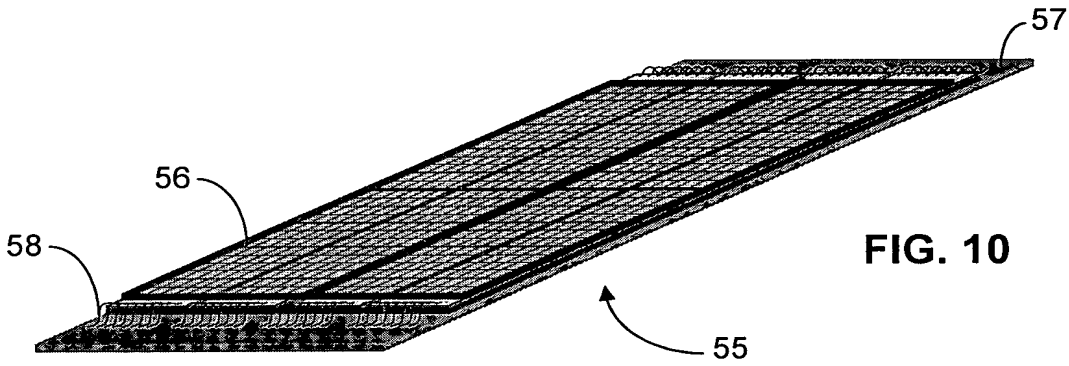

FIG. 10

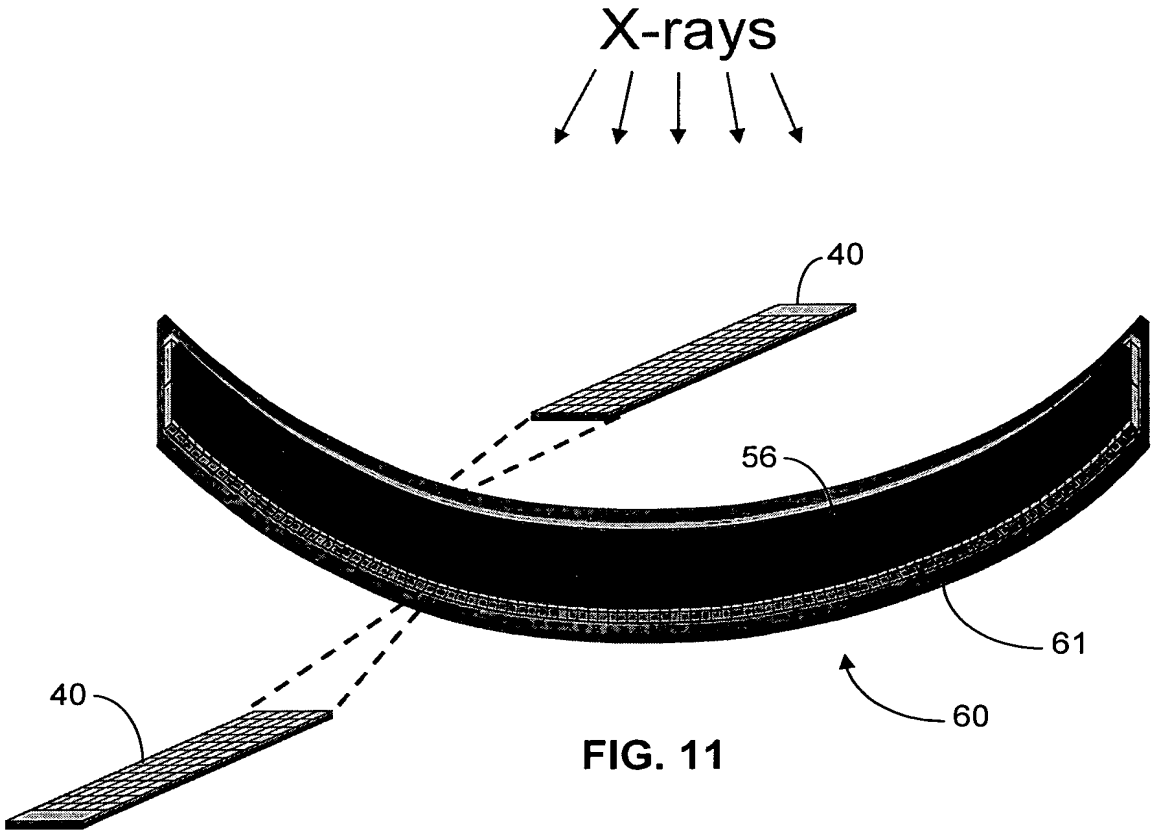

FIG. 11

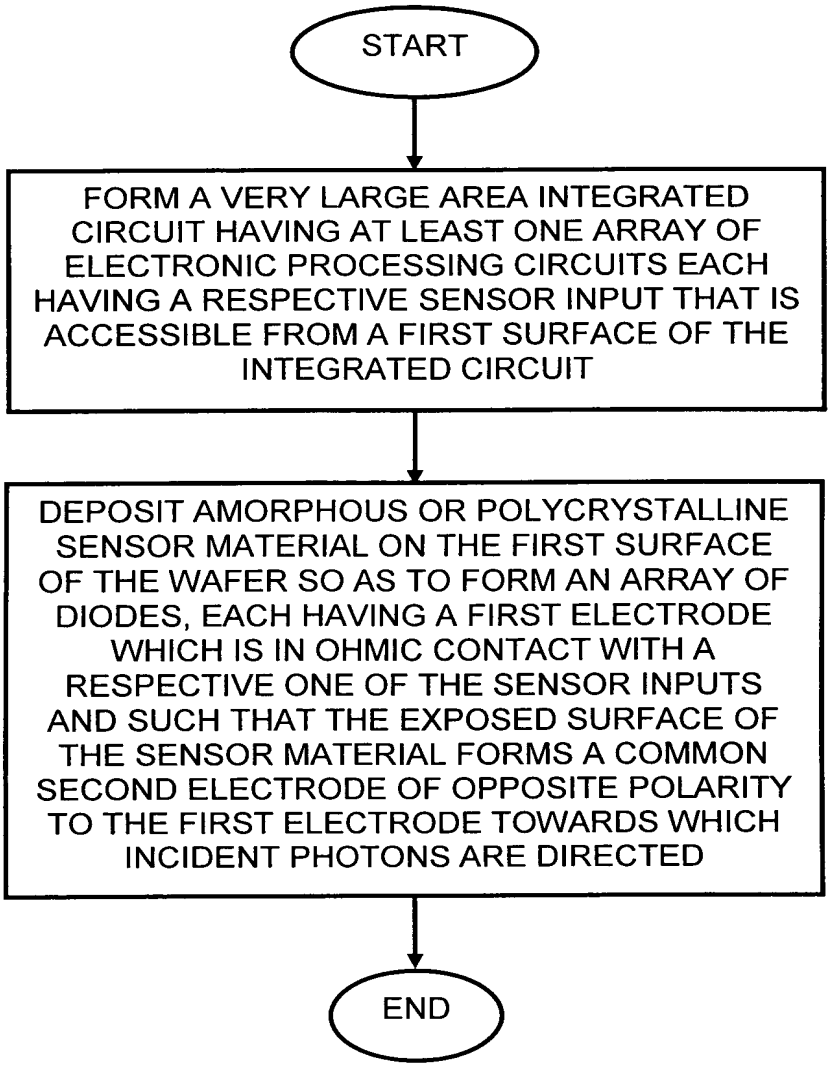
START
FORM A VERY LARGE AREA INTEGRATED CIRCUIT HAVING AT LEAST ONE ARRAY OF ELECTRONIC PROCESSING CIRCUITS EACH HAVING A RESPECTIVE SENSOR INPUT THAT IS ACCESSIBLE FROM A FIRST SURFACE OF THE INTEGRATED CIRCUIT
DEPOSIT AMORPHOUS OR POLYCRYSTALLINE SENSOR MATERIAL ON THE FIRST SURFACE OF THE WAFER SO AS TO FORM AN ARRAY OF DIODES, EACH HAVING A FIRST ELECTRODE WHICH IS IN OHMIC CONTACT WITH A RESPECTIVE ONE OF THE SENSOR INPUTS AND SUCH THAT THE EXPOSED SURFACE OF THE SENSOR MATERIAL FORMS A COMMON SECOND ELECTRODE OF OPPOSITE POLARITY TO THE FIRST ELECTRODE TOWARDS WHICH INCIDENT PHOTONS ARE DIRECTED
END

FIG. 12